

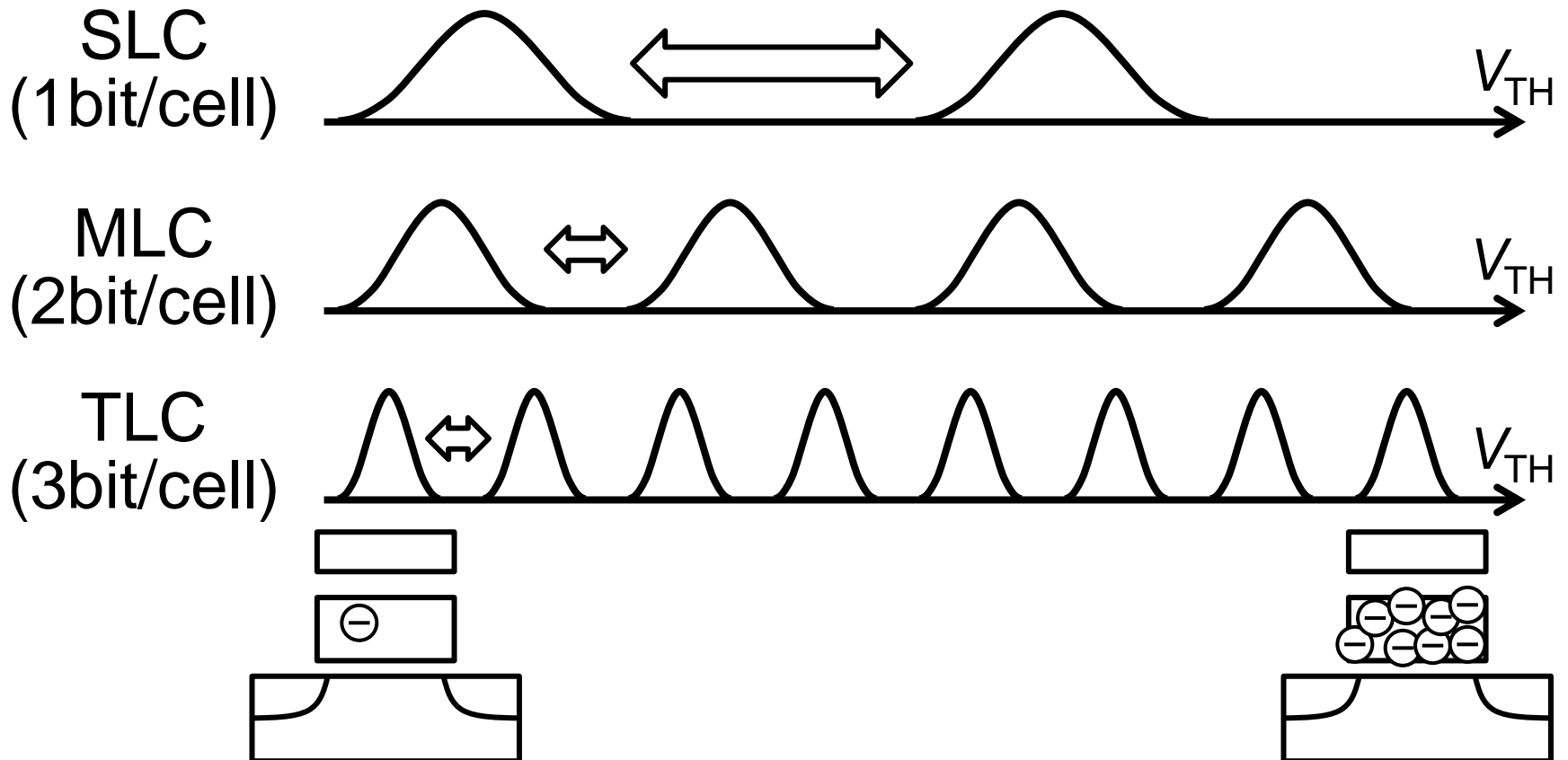
Highly Reliable Storage System with Triple-Level Cell (TLC) NAND Flash Memories

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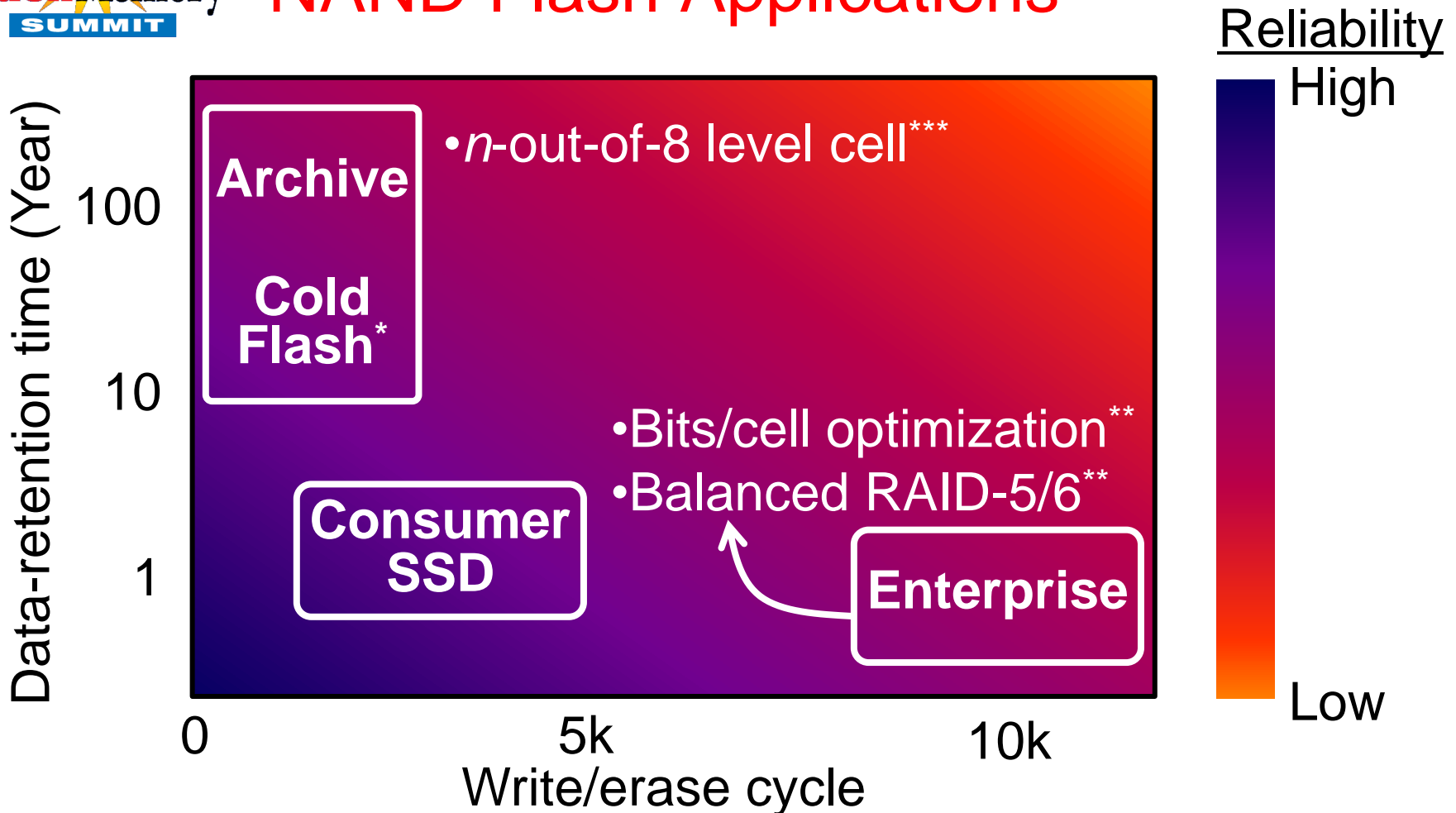
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Triple-level cell (TLC) NAND flash

- TLC NAND flash can store 3 bits/cell but has a smaller memory window.



NAND Flash Applications



(*) J. Taylor, *Flash Memory Summit*, 2013.

(**) S. Tanakamaru *et al.*, *ISSCC*, pp. 336-337, 2014.

(***) S. Tanakamaru *et al.*, *Symp. VLSI Circ.*, pp. 103-104, 2014.



Thank you for your attention

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